

COMPLEMENTARY NPN/PNP PRE-BIASED SMALL SIGNAL SOT-563 DUAL SURFACE MOUNT TRANSISTOR

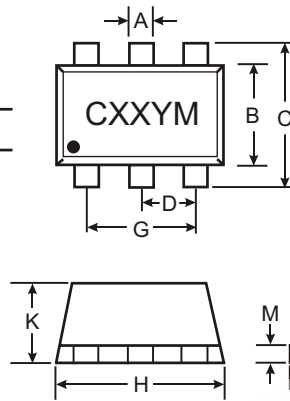
NEW PRODUCT

Features

- Epitaxial Planar Die Construction
- Built-In Biasing Resistors
- Lead Free By Design/RoHS Compliant (Note 3)

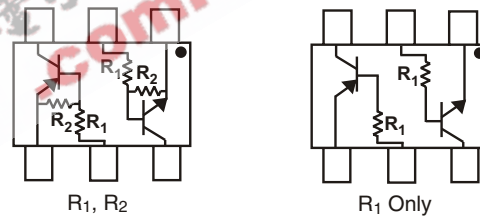
Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.005 grams (approx.)



SOT-563			
Dim	Min	Max	Typ
A	0.15	0.30	0.25
B	1.10	1.25	1.20
C	1.55	1.70	1.60
D	0.50		
G	0.90	1.10	1.00
H	1.50	1.70	1.60
K	0.56	0.60	0.60
L	0.15	0.25	0.20
M	0.10	0.18	0.11
All Dimensions in mm			

P/N	R1 (NOM)	R2 (NOM)	MARKING
DCX122LH	0.22K Ω	10K Ω	C81
DCX142JH	0.47K Ω	10K Ω	C82
DCX122TH	0.22K Ω	OPEN	C83
DCX142TH	0.47K Ω	OPEN	C84



SCHEMATIC DIAGRAM, TOP VIEW

Maximum Ratings NPN Section @ T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V _{CC}	50	V
Input Voltage	V _{IN}	-5 to +6	V
Input Voltage	V _{EBO} (MAX)	5	V
Output Current	I _C	100	mA
Power Dissipation (Note 1, 2)	P _d	150	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	R _{θJA}	833	°C/W
Operating and Storage and Temperature Range	T _j , T _{STG}	-55 to +150	°C

- Note: 1. Mounted on FR4 PC Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. NPN Section, PNP Section, or maximum combined.
 3. No purposefully added lead.

Maximum Ratings PNP Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage	V_{CC}	-50	V
Input Voltage	DCX122LH DCX142JH V_{IN}	+5 to -6 +5 to -6	V
Input Voltage	DCX122TH DCX142TH $V_{EBO (MAX)}$	-5	V
Output Current	All I_C	-100	mA
Power Dissipation (Note 1, 2)	P_d	150	mW
Thermal Resistance, Junction to Ambient Air (Note 1)	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Operating and Storage and Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

Note: 1. Mounted on FR4 PC Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.
2. NPN Section, PNP Section, or maximum combined.

Electrical Characteristics NPN Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified **R1, R2 Types**

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DCX122LH DCX142JH $V_{I(off)}$	0.3 0.3	—	—	V	$V_{CC} = 5V, I_O = 100\mu A$
	DCX122LH DCX142JH $V_{I(on)}$	—	—	2.0 2.0	V	$V_O = 0.3V, I_O = 20mA$ $V_O = 0.3V, I_O = 20mA$
Output Voltage	$V_{O(on)}$	—	—	0.3V	V	$I_O/I_I = 5mA/0.25mA$
Input Current	DCX122LH DCX142JH I_I	—	—	28 13	mA	$V_I = 5V$
Output Current	$I_{O(off)}$	—	—	0.5	μA	$V_{CC} = 50V, V_I = 0V$
DC Current Gain	DDCX122LH DDCX142JH G_I	56 56	—	—	—	$V_O = 5V, I_O = 10mA$
Gain-Bandwidth Product*	f_T	—	200	—	MHz	$V_{CE} = 10V, I_E = 5mA,$ $f = 100MHz$

* Transistor - For Reference Only

Electrical Characteristics NPN Section @ $T_A = 25^\circ\text{C}$ unless otherwise specified **R1-Only**

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	$I_C = 50\mu A$
Collector-Emitter Breakdown Voltage	BV_{CEO}	40	—	—	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	DCX122TH DCX142TH BV_{EBO}	5	—	—	V	$I_E = 50\mu A$ $I_E = 50\mu A$
Collector Cutoff Current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 50V$
Emitter Cutoff Current	DCX122TH DCX142TH I_{EBO}	—	—	0.5 0.5	μA	$V_{EB} = 4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	—	—	0.3	V	$I_C = 5mA, I_B = 0.25mA$
DC Current Transfer Ratio	DCX122TH DCX142TH h_{FE}	100 100	250 250	600 600	—	$I_C = 1mA, V_{CE} = 5V$
Gain-Bandwidth Product*	f_T	—	200	—	MHz	$V_{CE} = 10V, I_E = -5mA,$ $f = 100MHz$

* Transistor - For Reference Only

Electrical Characteristics PNP Section @ T_A = 25°C unless otherwise specified **R1, R2 Types**

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DCX122LH DCX142JH	V _{I(off)}	-0.3 -0.3	—	—	V	V _{CC} = -5V, I _O = -100μA
	DCX122LH DCX142JH	V _{I(on)}	—	—	-2.0 -2.0	V	V _O = -0.3V, I _O = -20mA V _O = -0.3V, I _O = -20mA
Output Voltage		V _{O(on)}	—	—	-0.3V	V	I _O /I _I = -5mA/-0.25mA
Input Current	DCX122LH DCX142JH	I _I	—	—	-28 -13	mA	V _I = -5V
Output Current		I _{O(off)}	—	—	-0.5	μA	V _{CC} = -50V, V _I = 0V
DC Current Gain	DCX122LH DCX142JH	G _I	56 56	—	—	—	V _O = -5V, I _O = -10mA
Gain-Bandwidth Product*		f _T	—	200	—	MHz	V _{CE} = -10V, I _E = -5mA, f = 100MHz

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Electrical Characteristics @ T_A = 25°C unless otherwise specified **R1-Only Types**

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV _{CBO}	-50	—	—	V	I _C = -50μA
Collector-Emitter Breakdown Voltage		BV _{CEO}	-40	—	—	V	I _C = -1mA
Emitter-Base Breakdown Voltage	DCX122TH DCX142TH	BV _{EBO}	-5	—	—	V	I _E = -50μA I _E = -50μA
Collector Cutoff Current		I _{CBO}	—	—	-0.5	μA	V _{CB} = -50V
Emitter Cutoff Current	DCX122TH DCX142TH	I _{EBO}	—	—	-0.5 -0.5	μA	V _{EB} = -4V
Collector-Emitter Saturation Voltage		V _{CE(sat)}	—	—	-0.3	V	I _C = -5mA, I _B = -0.25mA
DC Current Transfer Ratio	DCX122TH DCX142TH	h _{FE}	100 100	250 250	600 600	—	I _C = -1mA, V _{CE} = -5V
Gain-Bandwidth Product*		f _T	—	200	—	MHz	V _{CE} = -10V, I _E = 5mA, f = 100MHz

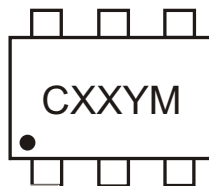
* Transistor - For Reference Only

Ordering Information (Note 4)

Device	Packaging	Shipping
DCX122LH-7	SOT-563	3000/Tape & Reel
DCX142JH-7	SOT-563	3000/Tape & Reel
DCX122TH-7	SOT-563	3000/Tape & Reel
DCX142TH-7	SOT-563	3000/Tape & Reel

Notes: 4. For Packaging Details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



CXX = Product Type Marking Code (See Page 1)
 YM = Date Code Marking
 Y = Year ex: P = 2003
 M = Month ex: 9 = September

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009
Code	N	P	R	S	T	U	V	W

Month	Jan	Feb	March	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

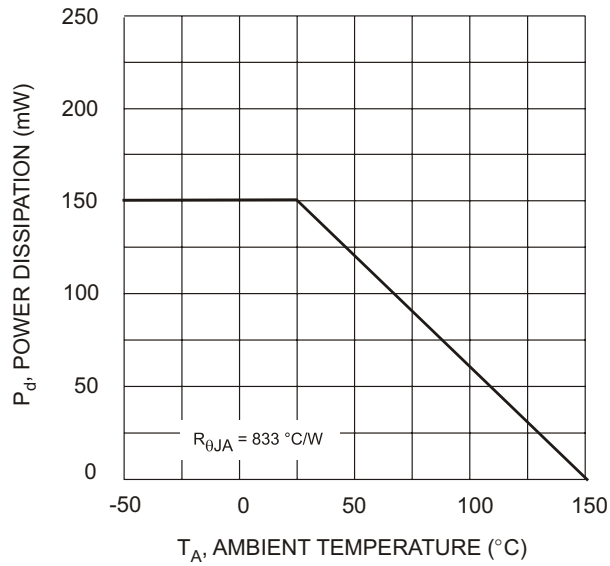


Fig. 1 Derating Curve - Total

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